

# P-Channel -30V (D-S) Power MOSFET

### **Features**

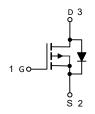
- 100% Avalanche Tested
- Halogen Free, Pb-Free
- RoHS Compliant



SOT-23

## **Applications**

- Relay driver
- Switching circuits
- High-side load switch
- High-speed line driver



Absolute Maximum Ratings (T <sub>A</sub> =25°C unless otherwise noted)							
Parameter	Symbol	Value	Unit				
Drain Source Voltage		V <sub>DS</sub>	-30	V			
Gate Source Voltage	$V_{GS}$	±12	V				
Drain Current, Continuous V <sub>GS</sub> =10V	Tc=25°C	I_	-4.2	А			
	Tc=70°C	l <sub>D</sub>	-3.5				
Drain Current, Pulsed (Note 1)	Ірм	-30	Α				
Power Dissipation	T <sub>C</sub> =25°C	P <sub>D</sub>	1.4	W			
Operating Junction/ Storage Tempera	TJ/ Tstg	-55 to +150	°C				

Note 1: Single pulse;  $t_p \le 1$ us.

Thermal Characteristics					
Parameter	Symbol	Max	Unit		
Thermal Resistance Junction to Ambient (t ≤ 10s) (Note 2)	R <sub>thJA</sub>	90	°C/W		

Note 2: Device mounted on 1 square inch FR4 PCB board, with 2oz single-sided copper, in a 25°C still air environment.



Electrical Characteristics (T <sub>A</sub> =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Drain Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	uA
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250uA	-0.6		-1.3	V
Gate Leakage Current	Igss	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V			±100	nA
Drain-Source On-state Resistance (Note 3)	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A		44	55	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A		52	75	
Total Gate Charge	Qg	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A		11		nC
Gate-Source Charge	Qgs			2.1		
Gate-Drain Charge	Q <sub>gd</sub>			2.7		
Turn-on Delay Time	t <sub>d(on)</sub>	$V_{GS}$ =-4.5V, $V_{DD}$ =-20V, $R_{G}$ =3 $\Omega$ , $R_{L}$ =20 $\Omega$		9.8		
Turn-on Rise Time	tr			11		
Turn-off Delay Time	t <sub>d(off)</sub>			25		ns
Turn-off Fall Time	t <sub>f</sub>			8		
Input Capacitance	Ciss	V <sub>GS=</sub> 0V, V <sub>DS</sub> =-20V, f=1MHz		758		
Output Capacitance	Coss			64		pF
Reverse Transfer Capacitance	Crss			53		

Reverse Diode Characteristics (T <sub>A</sub> =25°C unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Forward Current, Continuous	Isp	Tc=25°C			-4.2	Α
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	I <sub>F</sub> =-1A, V <sub>GS</sub> =0V		-0.78	-1.0	V

Note 3: Pulse test; pulse width ≤ 380µs, duty cycle ≤ 1%.



### Typical Characteristics Curves (TA = 25°C unless otherwise noted)

Fig.1 - Typical Output Characteristics

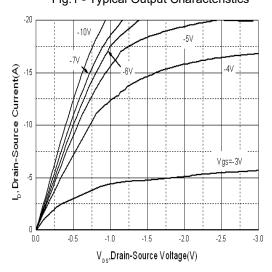


Fig.3 - Drain-to-Source Breakdown Voltage vs. Junction Temperature

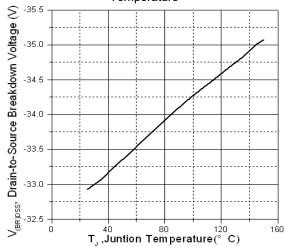


Fig.5 - Maximum Drain Current vs. Case Temperature

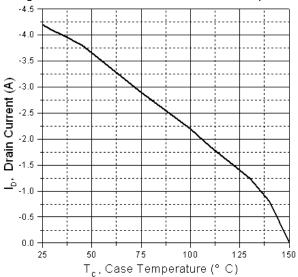


Fig.2 - V<sub>GS(th)</sub> vs. Junction Temperature

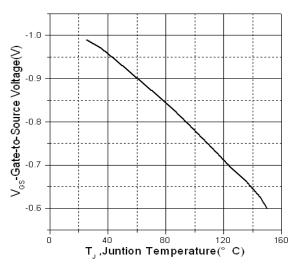


Fig.4 - R<sub>DS(on)</sub> vs. Junction Temperature

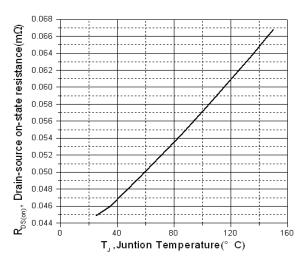
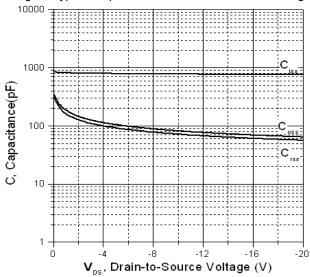


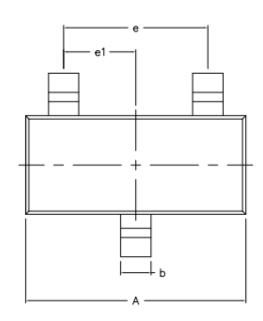
Fig.6 - Typical Capacitance vs. Drain-to-Source Voltage

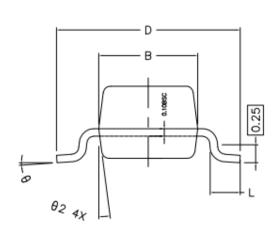


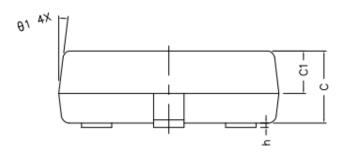


# Package Outline Dimensions (Unit: millimeters)

# **SOT-23**



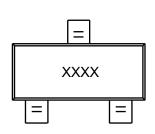




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COMMON DIMENSIONS					
	(UNITS OF MEASURE IS mm)				
	MIN	NORMAL	MAX		
Α	2.800	2.900	3.000		
В	1.200	1.300	1.400		
С	0.900	1.000	1.100		
C1	0.500	0.550 0.60			
D	2.300	2.400	2.500		
L	0.300	0.400	0.500		
h	0.010	0.050	0.100		
b	0.350	0.400	0.450		
е		1.90 TYPE			
e1	0.95 TYPE				
θ1		7° TYPE			
$\theta_2$		7° TYPE			
θ		0° ~ 7°			



# **Marking Outline**



Part Name: GMP3341UP

1. P/N Mark: 3341



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